

# **isc** Silicon NPN Darlington Power Transistor

## **TIP112**

### DESCRIPTION

- · High DC Current Gain-
- : h<sub>FE</sub> = 1000(Min)@ I<sub>C</sub>= 1A
- · Collector-Emitter Sustaining Voltage-
  - : V<sub>CEO(SUS)</sub> = 100V(Min)
- · Low Collector-Emitter Saturation Voltage-
- : V<sub>CE(sat)</sub> = 2.5V(Max)@ I<sub>C</sub>= 2A
- Complement to Type TIP117
- · Minimum Lot-to-Lot variations for robust device performance and reliable operation

### **APPLICATIONS**

• Designed for general purpose amplifier and low speed switching applications.

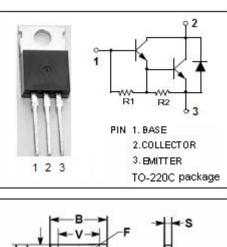
ABSOLUTE MAXIMUM RATINGS (Ta=25°C)							
SYMBOL	PARAMETER	VALUE	UNIT				
V <sub>CBO</sub>	Collector-Base Voltage	100	V				
V <sub>CEO</sub>	Collector-Emitter Voltage	100	V				
V <sub>EBO</sub>	Emitter-Base Voltage	5	V				
lc	Collector Current-Continuous	2	А				
Ісм	Collector Current-Peak	4	А				
IB	Base Current		mA				
Pc	Collector Power Dissipation $T_{c}\text{=}25^{\circ}\!\!\!\!\!\!\mathrm{C}$	50					
	Collector Power Dissipation $T_a=25^{\circ}C$	2	- W				
Tj	Junction Temperature	150	°C				
T <sub>stg</sub>	Storage Temperature Range	-65~150	°C				

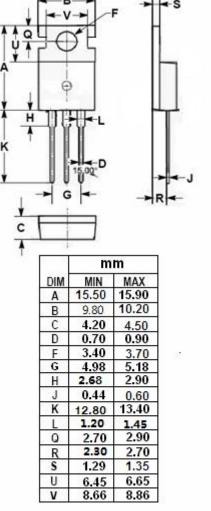
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#### **THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th j-c</sub>	Thermal Resistance, Junction to Case	2.5	°C/W
R <sub>th j-a</sub>	Thermal Resistance, Junction to Ambient	62.5	°C/W

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#### **ELECTRICAL CHARACTERISTICS**

#### T<sub>c</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	МАХ	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 30mA, I <sub>B</sub> = 0	100			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 2A, I <sub>B</sub> = 8mA			2.5	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = 2A; V <sub>CE</sub> = 4V			2.8	V
Ісво	Collector Cutoff Current	V <sub>CB</sub> = 100V, I <sub>E</sub> = 0			1.0	mA
I <sub>CEO</sub>	Collector Cutoff Current	$V_{CE}$ = 50V, I <sub>B</sub> = 0			2.0	mA
Іево	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0			2.0	mA
hfe-1	DC Current Gain	Ic= 1A; V <sub>CE</sub> = 4V	1000			
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 2A; V <sub>CE</sub> = 4V	500			
Сов	Output Capacitance	I <sub>E</sub> = 0; V <sub>CB</sub> = 10V, f= 0.1MHz			200	pF

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